UNIKC Semiconductor

RoHS Compliant

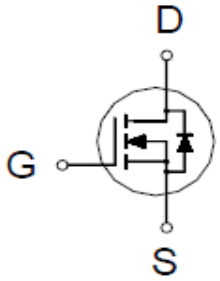
PE600BA

N-Channel Enhancement Mode MOSFET

PRODUCT SUMMARY

$V_{(BR)DSS}$	$R_{DS(ON)}$	I_D
30V	9.8mΩ @V_{GS} = 10V	32A

PDFN 3X3P



ABSOLUTE MAXIMUM RATINGS (T_A = 25 °C Unless Otherwise Noted)

PARAMETERS/TEST CONDITIONS		SYMBOL	LIMITS	UNITS
Drain-Source Voltage		V_{DS}	30	V
Gate-Source Voltage		V_{GS}	±20	V
Continuous Drain Current[3]	T_C = 25 °C	I_D	32	A
	T_C = 100 °C		20	
Continuous Drain Current	T_A = 25 °C		14	
	T_A= 70 °C		11	
Pulsed Drain Current[1]		I_{DM}	90	
Avalanche Current		I_{AS}	18.5	
Avalanche Energy	L =0.1mH	E_{AS}	17	mJ
Power Dissipation	T_C = 25 °C	P_D	17.8	W
	T_C = 100 °C		7	
Power Dissipation[4]	T_A = 25 °C		3.5	
	T_A = 70 °C		2.3	
Operating Junction & Storage Temperature Range		T_J, T_{stg}	-55 to 150	°C

THERMAL RESISTANCE RATINGS

THERMAL RESISTANCE		SYMBOL	TYPICAL	MAXIMUM	UNITS
Junction-to-Ambient[2]	t ≦10s	$R_{\theta JA}$		35	°C / W
Junction-to-Ambient[2]	Steady-State	$R_{\theta JA}$		75	
Junction-to-Case	Steady-State	$R_{\theta JC}$		7	

[1]Pulse width limited by maximum junction temperature.

[2]The value of $R_{\theta JA}$ is measured with the device mounted on 1in^2 FR-4 board with 2oz. Copper, in a still air environment with T_A =25° C.

[3]Package limitation current is 16A.

[4]The Power dissipation is based on $R_{\theta JA}$ t ≦10s value.

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ELECTRICAL CHARACTERISTICS (T_J = 25 °C, Unless Otherwise Noted)

PARAMETER	SYMBOL	TEST CONDITIONS	LIMITS			UNITS
			MIN	TYP	MAX	
STATIC						
Drain-Source Breakdown Voltage	$V_{(BR)DSS}$	V_{GS} = 0V, I_D = 250μA	30			V
Gate Threshold Voltage	$V_{GS(th)}$	V_{DS} = V_{GS}, I_D = 250μA	1.3	1.75	2.3	
Gate-Body Leakage	I_{GSS}	V_{DS} = 0V, V_{GS} = ±20V			±100	nA
Zero Gate Voltage Drain Current	I_{DSS}	V_{DS} = 24V, V_{GS} = 0V			1	μA
		V_{DS} = 20V, V_{GS} = 0V, T_J =55 °C			10	
Drain-Source On-State Resistance[1]	$R_{DS(ON)}$	V_{GS} = 4.5V, I_D = 9A		10.2	14	mΩ
		V_{GS} = 10V , I_D =9A		7.8	9.8	
Forward Transconductance[1]	g_{fs}	V_{DS} = 10V, I_D = 9A		35		S
DYNAMIC						
Input Capacitance	C_{iss}	V_{GS} = 0V, V_{DS} = 15V, f = 1MHz		620		pF
Output Capacitance	C_{oss}			108		
Reverse Transfer Capacitance	C_{rss}			77		
Gate Resistance	R_g	V_{GS} = 0V, V_{DS} = 0V, f = 1MHz		2.5		Ω
Total Gate Charge[2]	Q_g(V_{GS}=10V)	V_{DS} = 15V , I_D = 9A		14		nC
	Q_g(V_{GS}=4.5V)			8		
Gate-Source Charge[2]	Q_{gs}			2		
Gate-Drain Charge[2]	Q_{gd}			3.8		
Turn-On Delay Time[2]	$t_{d(on)}$	V_{DD}= 15V, I_D ≅ 9A, V_{GEN} = 10V, R_G= 6Ω		13		nS
Rise Time[2]	t_r			37		
Turn-Off Delay Time[2]	$t_{d(off)}$			48		
Fall Time[2]	t_f			25		
SOURCE-DRAIN DIODE RATINGS AND CHARACTERISTICS (T_J = 25 °C)						
Continuous Current[3]	I_S				16	A
Forward Voltage[1]	V_{SD}	I_F = 9A, V_{GS} = 0V			1.1	V
Reverse Recovery Time	t_{rr}	I_F = 9A, dI_F/dt = 100A / μS		12		nS
Reverse Recovery Charge	Q_{rr}			3		nC

[1]Pulse test : Pulse Width ≤ 300 μsec, Duty Cycle ≤ 2%.

[2]Independent of operating temperature.

[3]Package limitation current is 16A.

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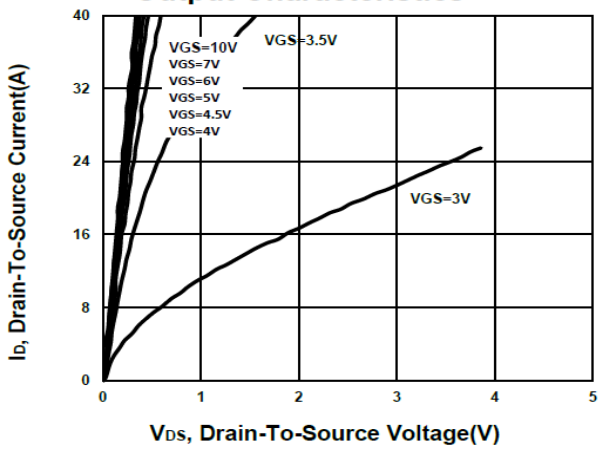
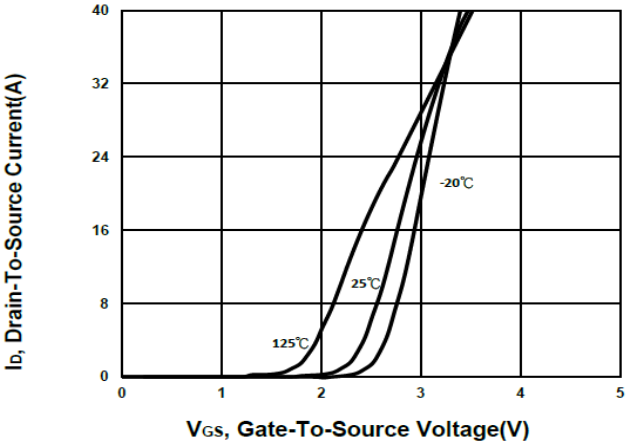
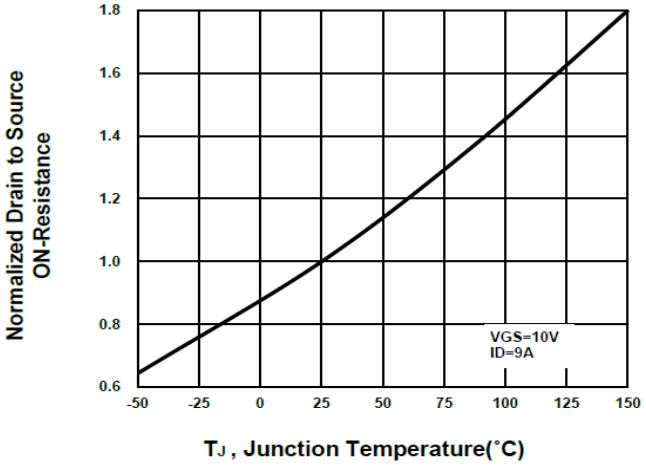
Output Characteristics



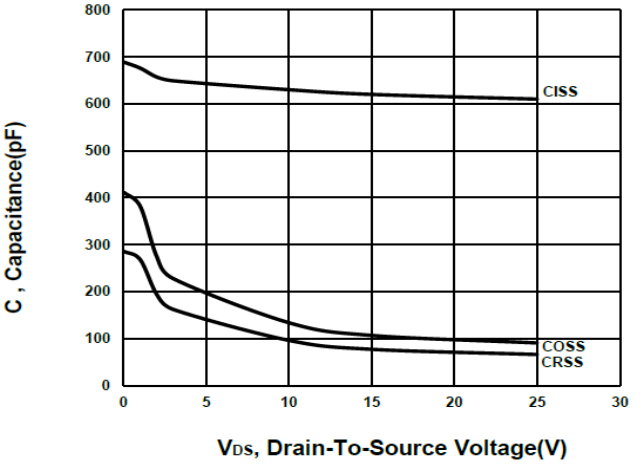
Transfer Characteristics



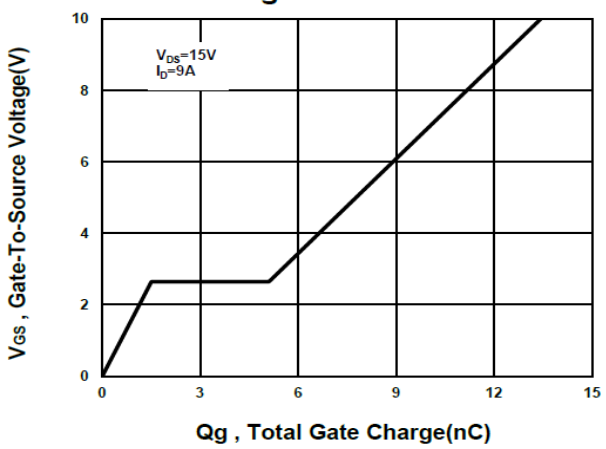
On-Resistance VS Temperature



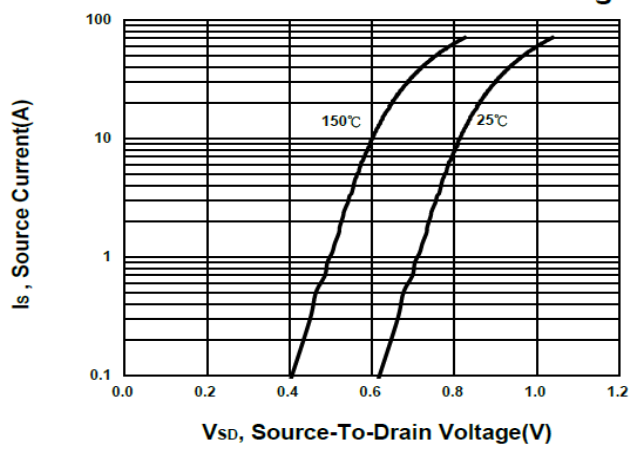
Capacitance Characteristic



Gate charge Characteristics



Source-Drain Diode Forward Voltage



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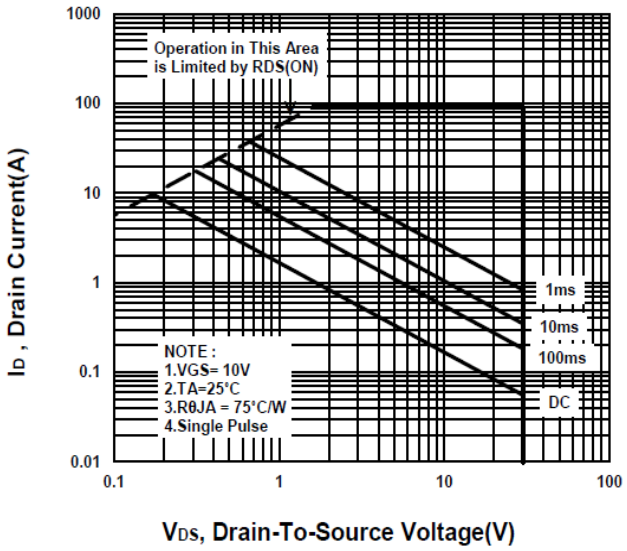
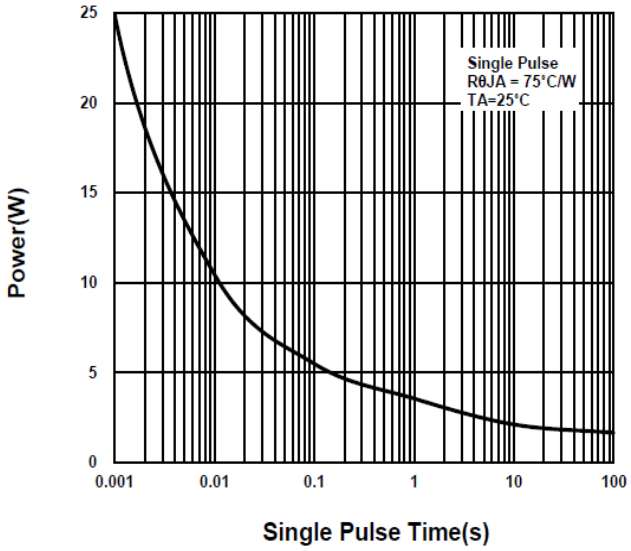
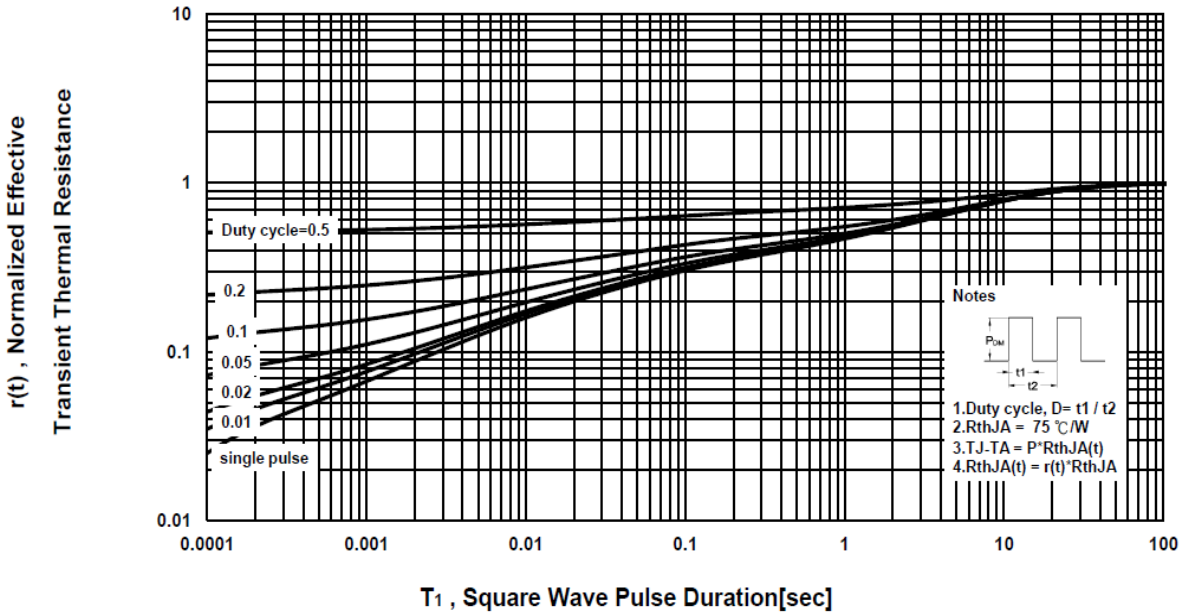
Safe Operating Area



Single Pulse Maximum Power Dissipation



Transient Thermal Response Curve



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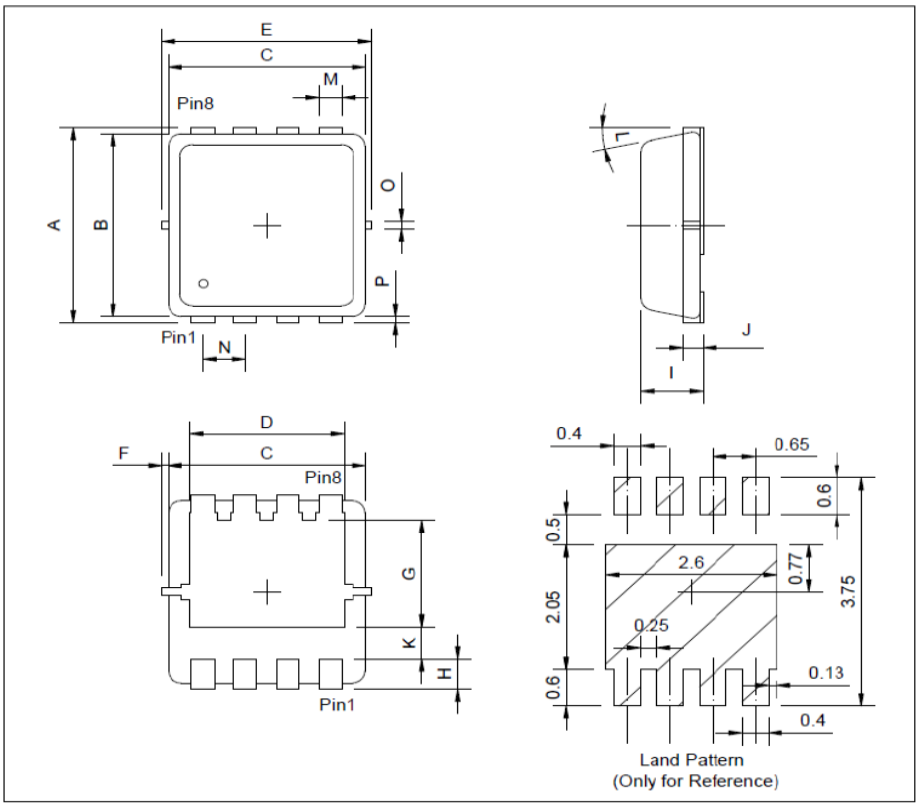
Package Dimension

PDFN 3x3P MECHANICAL DATA

Dimension	mm			Dimension	mm		
	Min.	Typ.	Max.		Min.	Typ.	Max.
A	3	3.3	3.6	I	0.65	0.8	0.9
B	2.88	3	3.2	J	0.1	0.15	0.25
C	2.9	3	3.25	K	0.59		
D	2.29	2.45	2.69	L	0°	10°	12°
E	3	3.3	3.6	M	0.14	0.3	0.4
F	0	0.1	0.2	N	0.55	0.65	0.75
G	1.35	1.75	2.2	O		0.2	
H	0.15	0.3	0.55	P	0		0.2



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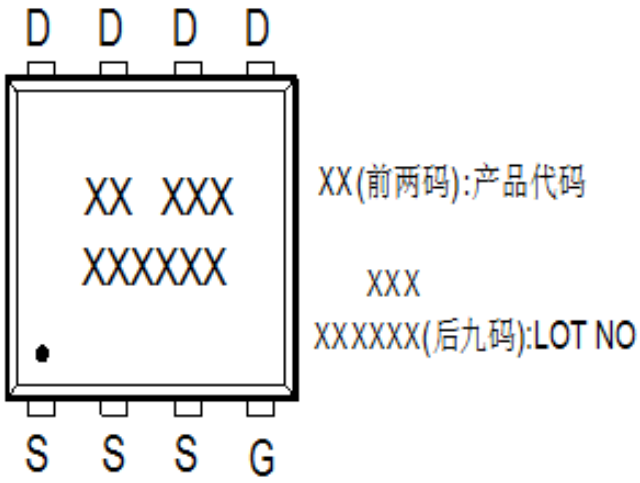
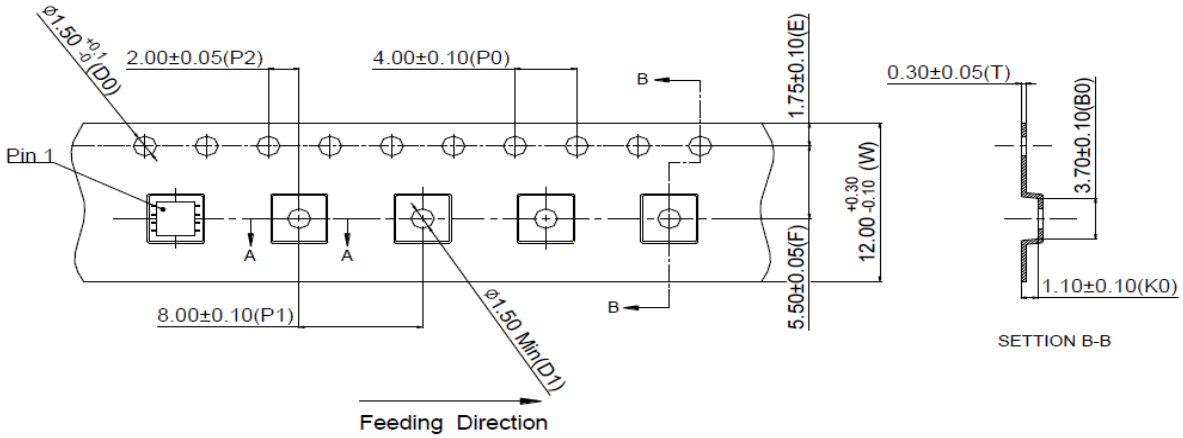
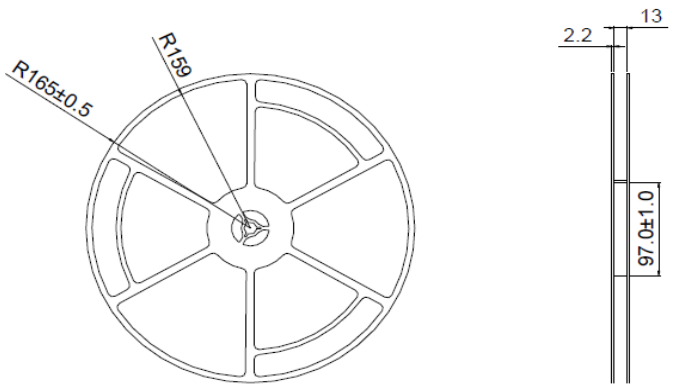
A. Marking Information(此产品代码为：F1）



B. Tape&Reel Information:5000pcs/Reel





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C. Lot.No. & Date Code rule

1.LOT.NO.

M N 15M21 03

- 03 → #8~9 Sub-lot No
- 15M21 → Order series no.
- N → Foundry site
- M → Assembly site

2.Date Code

D Y M X XXX

- XXX → Order series no. & Sub-lot No
- X → Week
- M → M : Month (A:Jan , B:Feb , C:Mar ,D :Apr ,E:May ,F:Jun,G:Jul,H:Aug,I:Sep,J:Oct,K:Nov,L:Dec.)
- Y → Y : Year (N : 2011, O : 2012 ...)
- D → Assembly site

3.Date Code (for Small package)

XX Y WW

- WW → Week
- Y → Y : Year (9: 2009,A : 2010, B : 2011 ...)
- XX → Device Name

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D.Label rule

标签内容(Label content)

1	Label Size	30 * 90 mm
2	Font style	Times New Roman or Arial (或可区分英文”O”和数字”0”，”G和”Q”的字型即可)
3	Great Power	Height: 4 mm
4	Package	Height: 2 mm
5	Date	Height: 2 mm Shipping date: YYYY/MM/DD, ex. 2008/09/12
6	Device	Height: 3 mm (Max: 16 Digit)
7	Lot	Height: 3 mm (Max: 9 Digit) Sub lot
8	D/C	Height: 3 mm (Max: 7 Digit)
9	QTY	Height: 3 mm (Max: 6 Digit) Thousand mark is no needed
10	Pb Free label	Pb Diameter: 1 cm bottom color: Green Font color: Black Font style: Arial
11	Halogen Free label	G Diameter: 1 cm bottom color: Green Font color: Black Font style: Arial
12	Scan info	Device / Lot / D/C / QTY , Insert “ / “ between every parts. for example: P3055LDG/G12345601/GGG2301/2000 DPI (Dots per inch): Over 300 dpi Code : Code 128 Height: 6 mm at least